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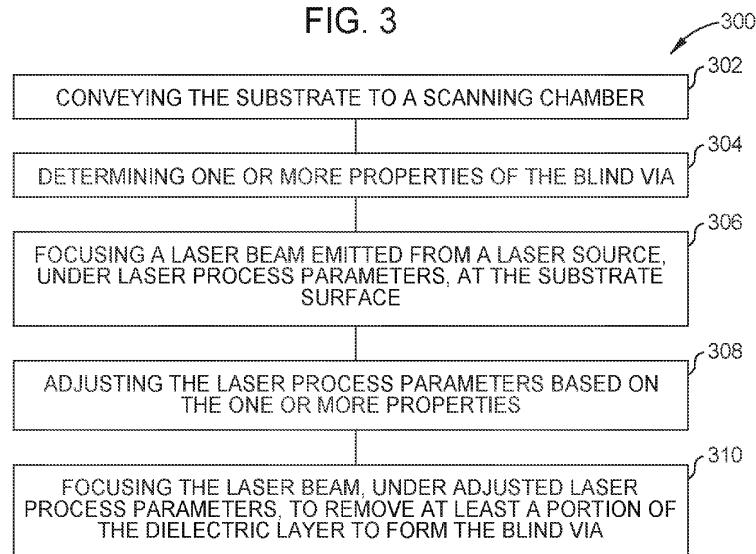
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(54) Title: METHOD AND APPARATUS FOR LASER DRILLING BLIND VIAS

FIG. 3



(57) Abstract: In an embodiment is provided a method of forming a blind via in a substrate comprising a mask layer, a conductive layer, and a dielectric layer that includes conveying the substrate to a scanning chamber; determining one or more properties of the blind via, the one or more properties comprising a top diameter, a bottom diameter, a volume, or a taper angle of about 80° or more; focusing a laser beam at the substrate to remove at least a portion of the mask layer; adjusting the laser process parameters based on the one or more properties; and focusing the laser beam, under the adjusted laser process parameters, to remove at least a portion of the dielectric layer within the volume to form the blind via. In some embodiments, the mask layer can be pre-etched. In another embodiment is provided an apparatus for forming a blind via in a substrate.

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